GRF2010

Preliminary

Broadband Linear Gain Block
0.05 to 5.0 GHz

Features

Reference: 5V/60mA/2000 MHz

- Gain: 10.1 dB
- OIP3: 30.5 dBm
- OP1dB: 19.0 dBm
- NF: 3.0 dB

- Flexible Bias
- Internally Matched to 50 Ω
- Process: GaAs pHEMT

Applications

- Requiring Flat Gain
- Linear Driver Amplifier
- Small Cells and Cellular Repeaters
- IF Amplifier

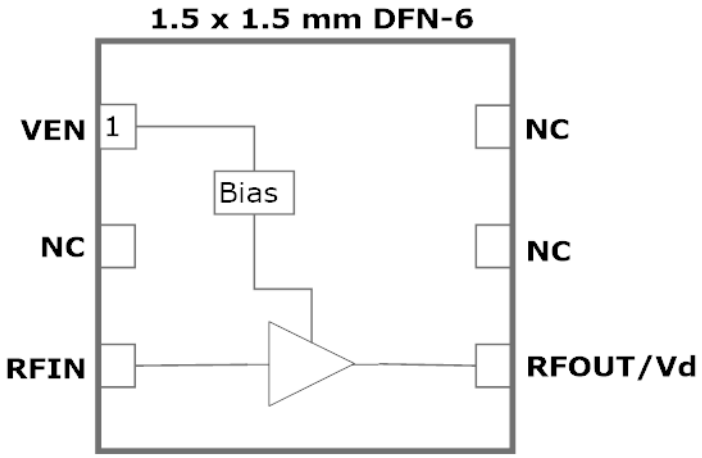
Product Description

GRF2010 is a broadband gain block with exceptional gain flatness for small cell, wireless infrastructure and other high performance applications. It exhibits outstanding broadband NF, linearity over 400 to 4000 MHz with a single match and can be optimized for applications from 50 MHz up to 5 GHz.

The device is operated from a supply voltage of 2.7 to 8.0 V with a selectable Iddq range of 15 to 70 mA for optimal efficiency and linearity.

GRF2010 is internally matched to 50 Ω at the input and output ports, needing only external DC blocks and a bias choke on the output.

Consult with the GRF applications engineering team for custom tuning/evaluation board data and device s-parameters



Absolute Ratings:

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V_{DD}	0	9.0	V
RF Input Power: (Load VSWR < 2:1; V_D: <= 8.0 volts)	$P_{IN\ MAX}$		TBD	dBm
Operating Temperature (Package Heat Sink)	T_{AMB}	-40	105	°C
Maximum Channel Temperature (MTTF > 10^6 Hours)	T_{MAX}		170	°C
Maximum Dissipated Power	$P_{DISS\ MAX}$		1.0	W
Electrostatic Discharge:				
Charged Device Model:	CDM	TBD		V
Human Body Model:	HBM	TBD		V
Storage:				
Storage Temperature	T_{STG}	-65	150	°C
Moisture Sensitivity Level	MSL		1	--

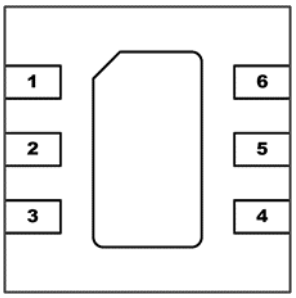
Caution! ESD Sensitive Device

Exceeding Absolute Maximum Rating conditions may cause permanent damage to the device.

Note: For manufacturing information, see the Guerrilla-RF.com website for the following document located on the GRF2010 landing page: Manufacturing Note—MN-001 Product Tape and Reel, Solderability and Package Outline Specification.

Link to manufacturing note

Pin Out (Top View)



Pin Assignments:

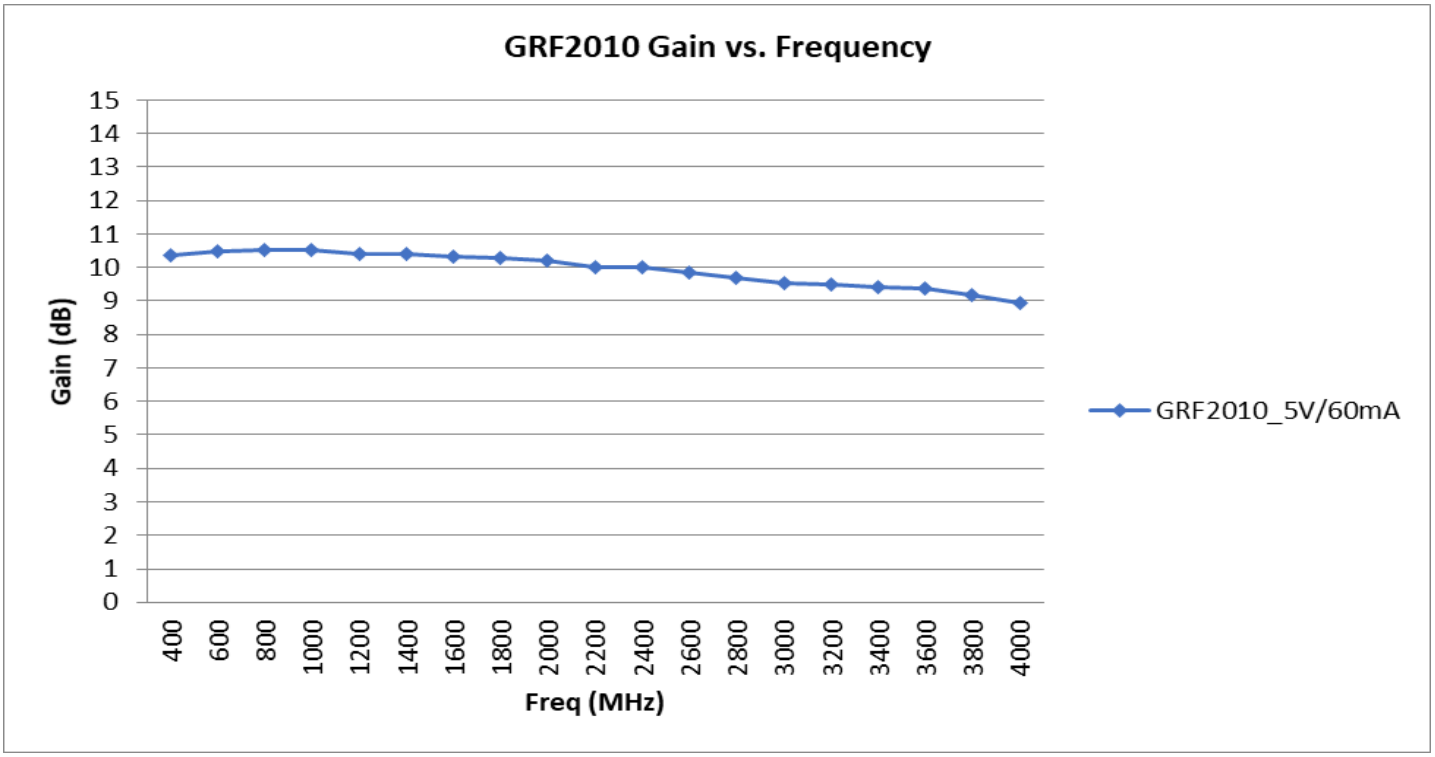
Pin	Name	Description	Note
1	V_{ENABLE}	Enable Voltage Input	V_{ENABLE} and series resistor set I_{DDQ}. V_{ENABLE} < =0.2 volts disables device. On -die pull-down resistor will turn the part off if this node is allowed to float. Note: The pin1 voltage should not exceed 3.0 volts due to excessive resulting I_{ENABLE}.
2	NC	No Connect or Ground	No internal connection to die
3	RF_In	LNA RF input	Internally matched 50Ω. An external DC blocking cap must be used.
4	RF_Out	LNA RF output	Internally matched 50Ω. V_{DD} must be applied through a choke to this pin
5	NC	No Connect or Ground	No internal connection to die
6	NC	No Connect or Ground	No internal connection to die
PKG BASE	GND	Ground	Provides DC and RF ground for LNA, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.

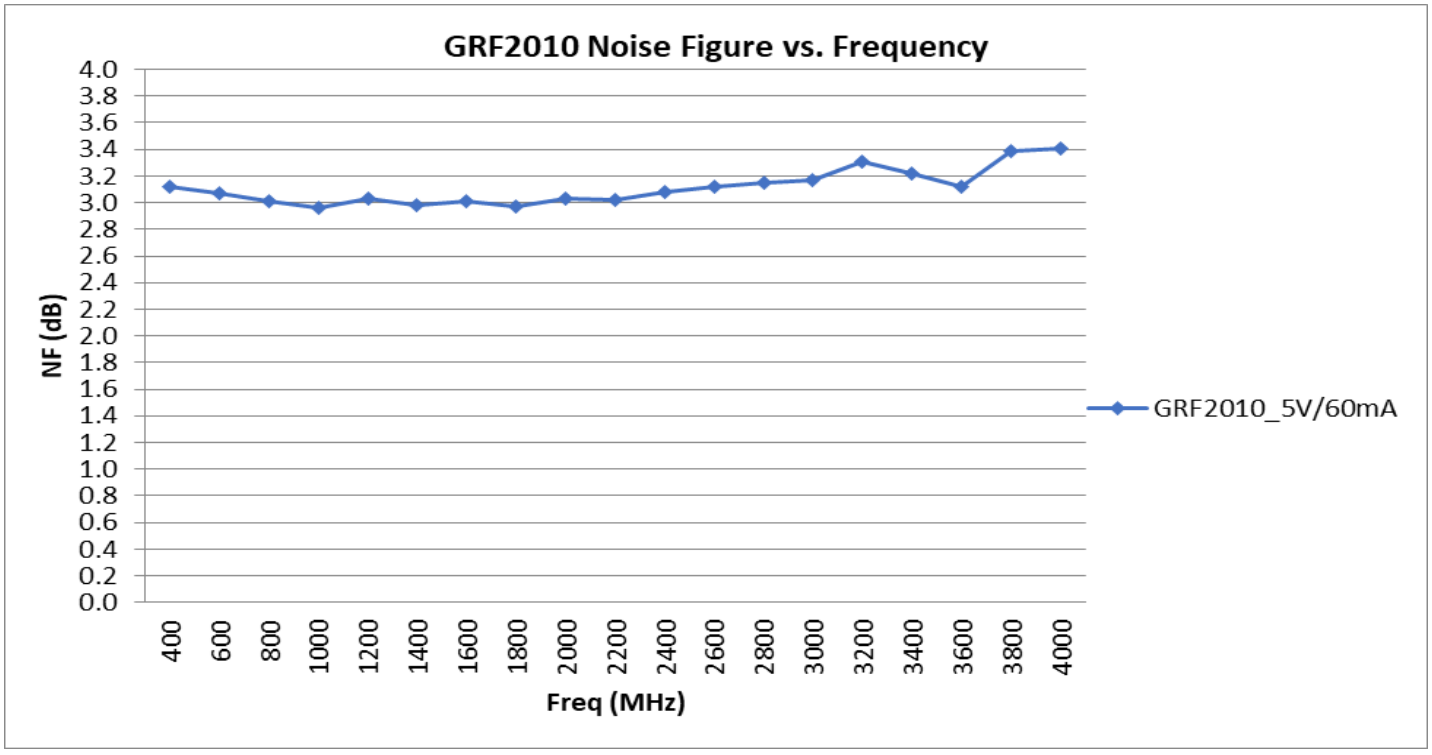
Nominal Operating Parameters:

Parameter	Symbol	Specification			Unit	Condition
		Min.	Typ.	Max.		
Test Frequency	F_{TEST}		2000		MHz	V_{DD} = 5.0 V, T_A = 25°C
Gain	S21		10.1		dB	
Evaluation Board Noise Figure	NF		3.0		dB	
Output 3rd Order Intercept	OIP3		30.5		dBm	+2.0 dBm P_{OUT} per tone at 2 MHz Spacing (1999 and 2001 MHz)
Output 1dB Compression Power	OP1dB		19.0		dBm	
Switching Rise Time (Estimated)	T_{RISE}		400		ns	
Switching Fall Time (Estimated)	T_{FALL}		400		ns	
Supply Current	I_{DD}		60.0		mA	V_{DD}=V_{ENABLE}=5.0 volts; R_{BIAS}: TBD
Enable Current	I_{ENABLE}		4.0		mA	
Disabled Mode						
Leakage Current	$I_{LEAKAGE}$		TBD		uA	V_{DD}: 5.0V; V_{ENABLE}: 0.0V
Thermal Data						
Thermal Resistance: (Estimated)	Θjc		55		°C/W	Standard Evaluation Board; No RF

Note: MTTF >10^6 hours for $T_{CHANNEL}$ < =170 degrees C.

GRF2010 Evaluation Board Measured Data: (0.4 to 4.0 GHz Tune)





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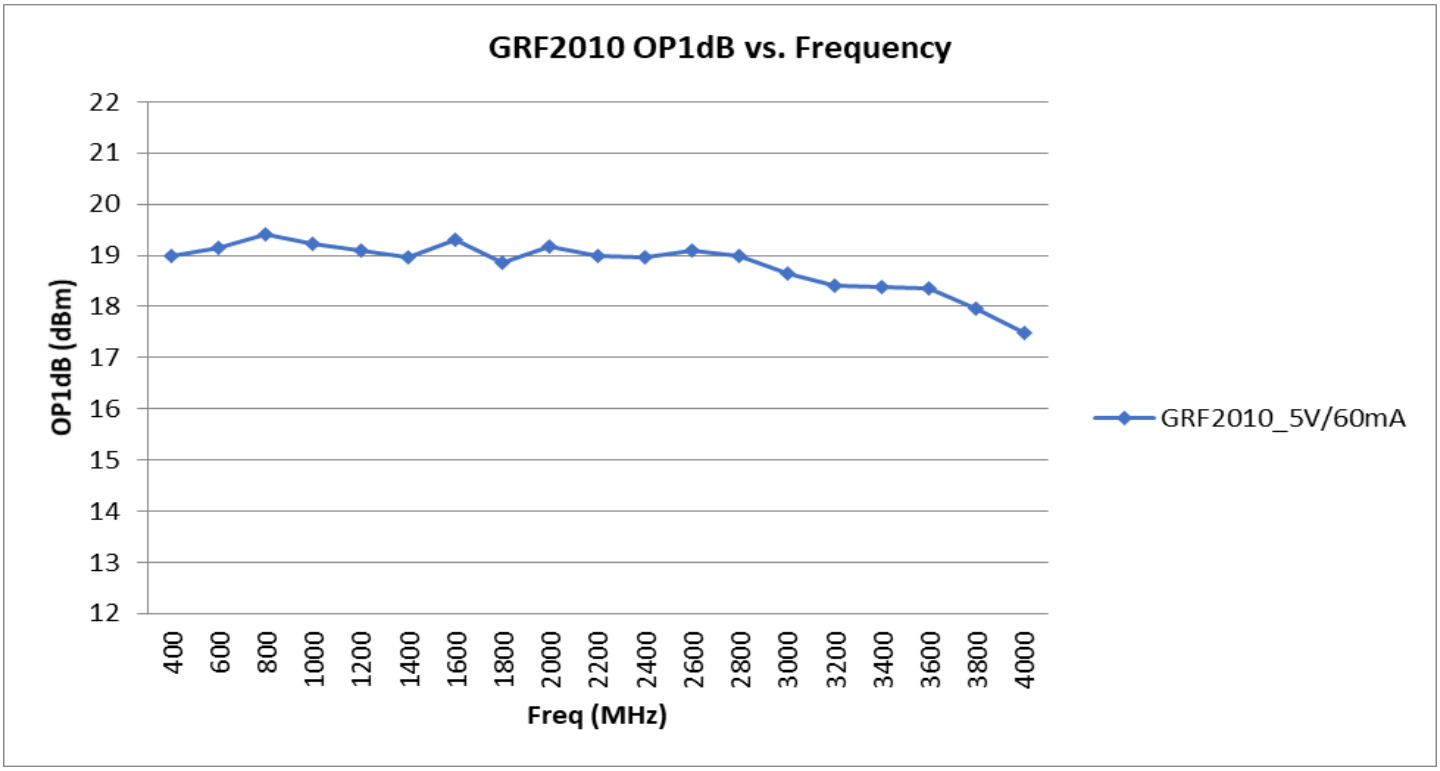
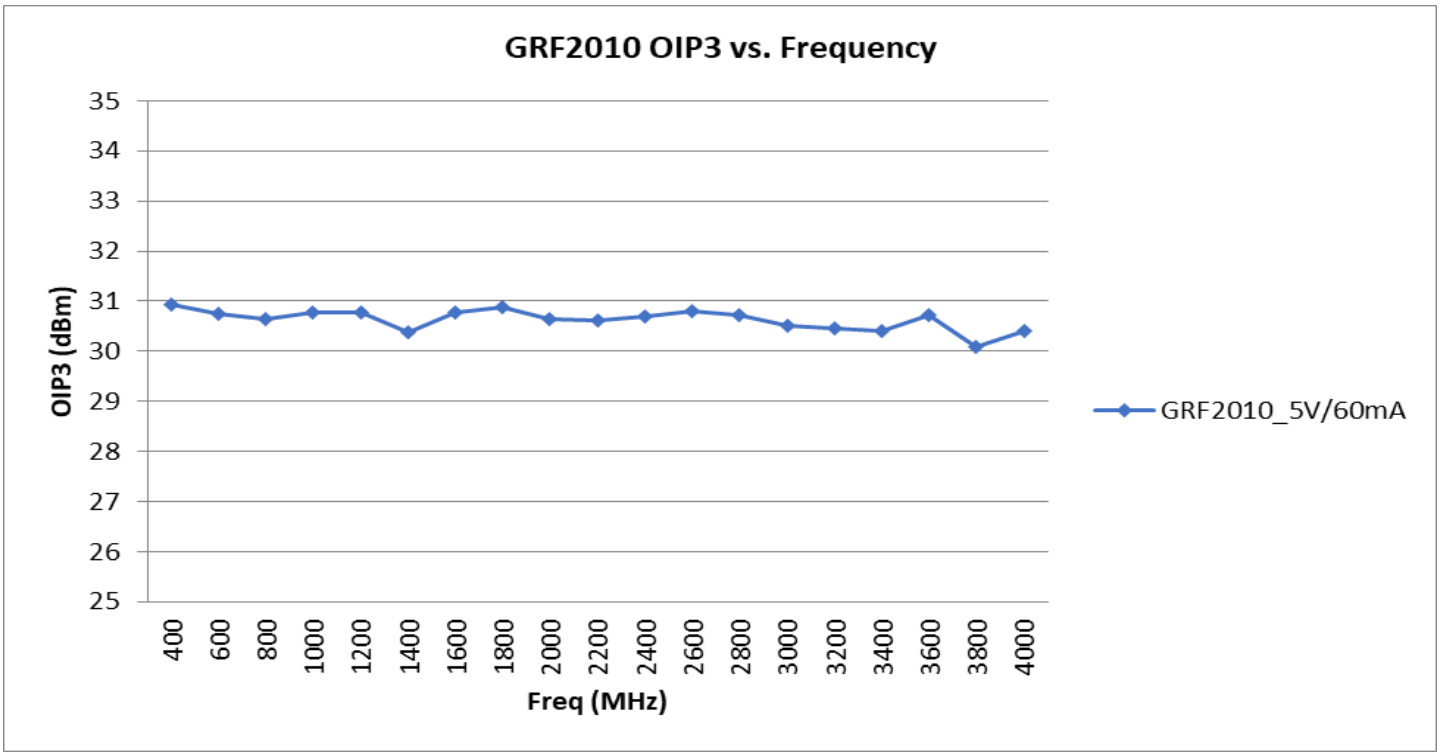
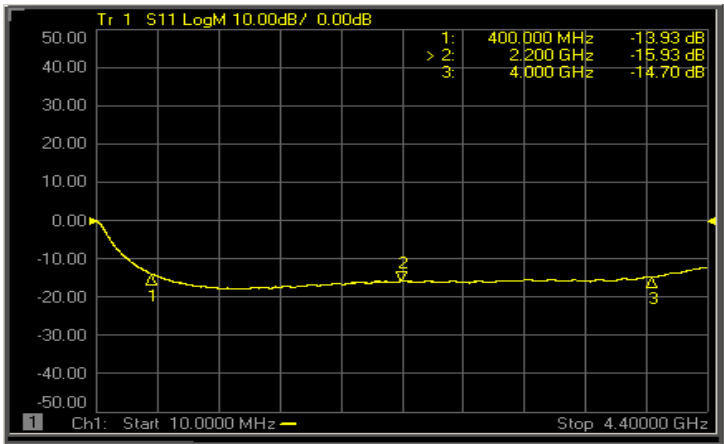
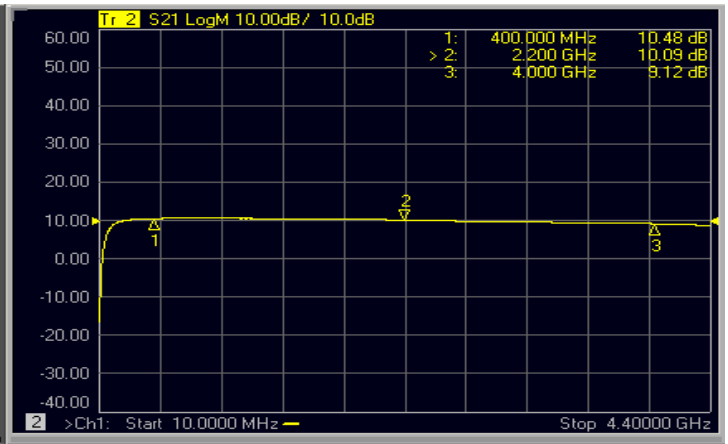
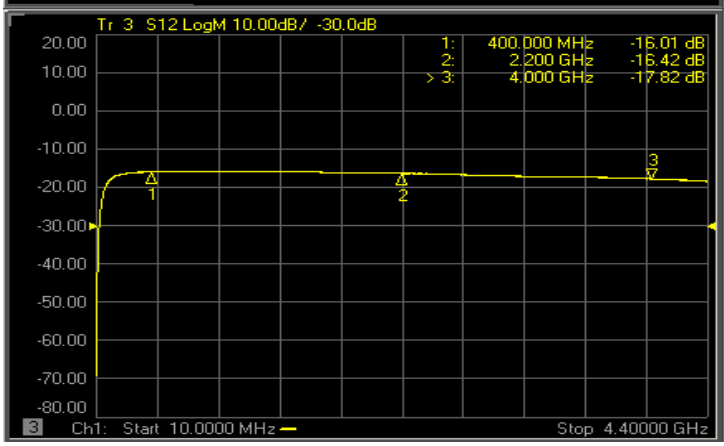


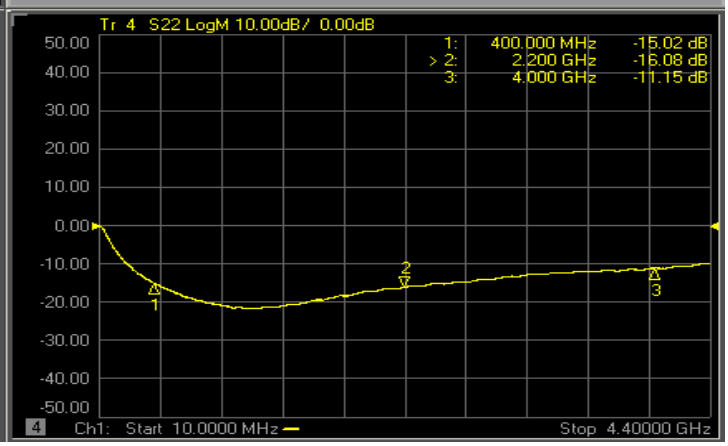


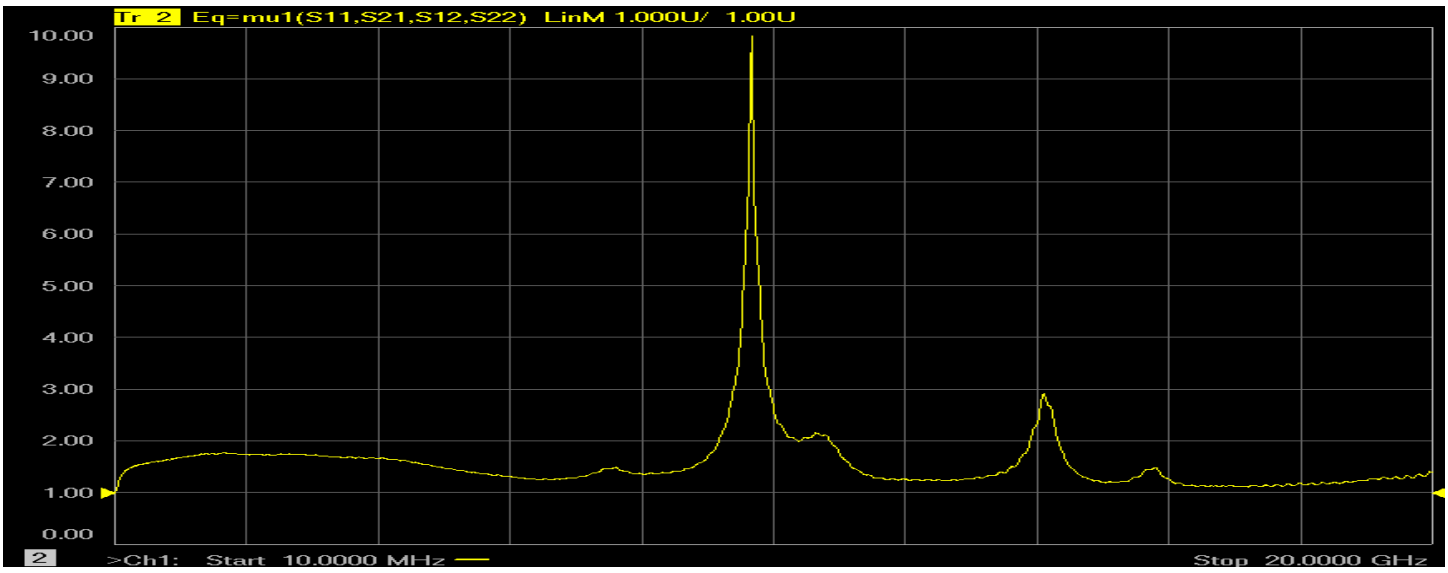
GRF2010 Evaluation Board S-Pars and Stability Mu Factor: (0.4 to 4.0 GHz Match)



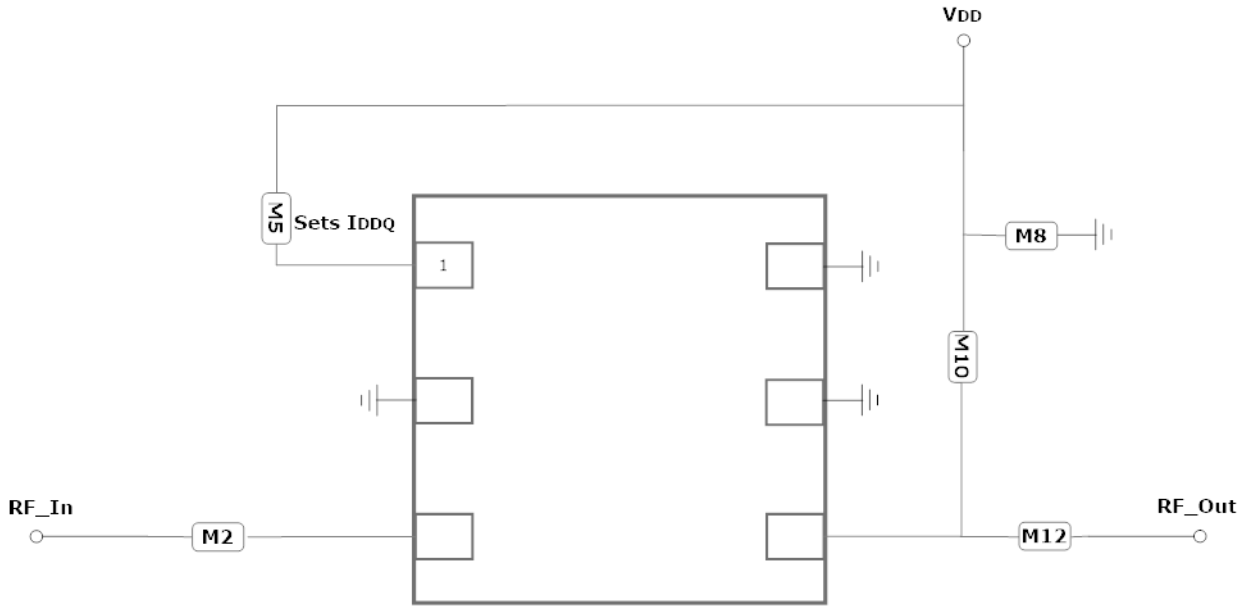




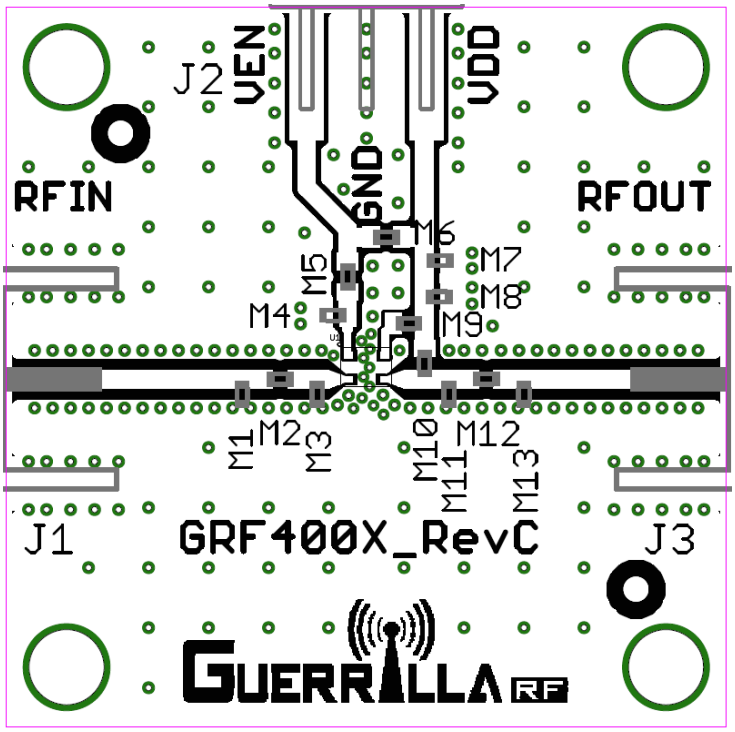




Note: Mu factor >= 1.0 implies unconditional stability.



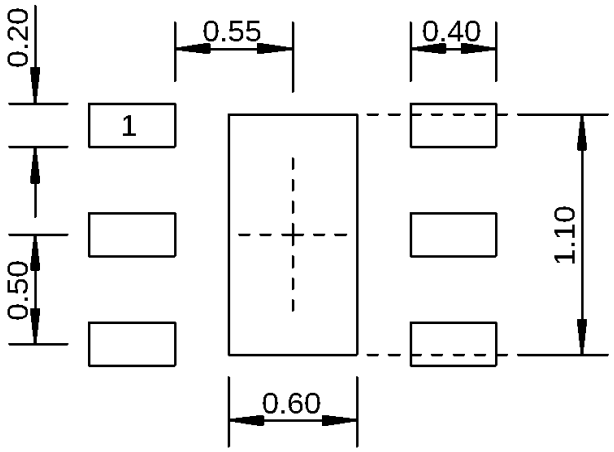
GRF2010 Application Schematic (0.4 to 4.0 GHz)



GRF2010 Evaluation Board Assembly Diagram

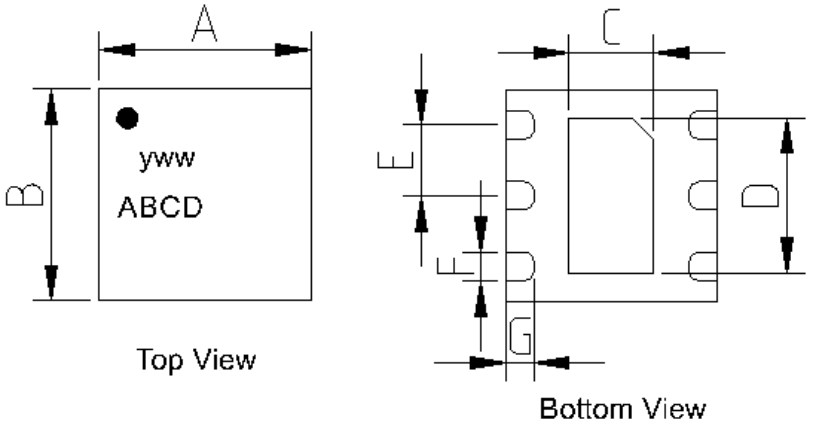
GRF2010 Standard Evaluation Board BOM: (0.4 to 4.0 GHz Tune)

Component	Type	Manufacturer	Family	Value	Package Size	Substitution
M2	Capacitor	Murata	GRM	100 pF	0402	ok
M5 (sets Iddq)	Resistor	Various	5%	TBD	0402	ok
M8	Capacitor	Murata	GRM	0.1 uF	0402	ok
M10	Inductor	Murata	LQG	47 nH	0402	ok
M12	Capacitor	Murata	GRM	100 pF	0402	ok
Evaluation Board	GRF400X_RevC					



Dimensions in millimeters

1.5 mm DFN-6 Suggested PCB Footprint (Top View)



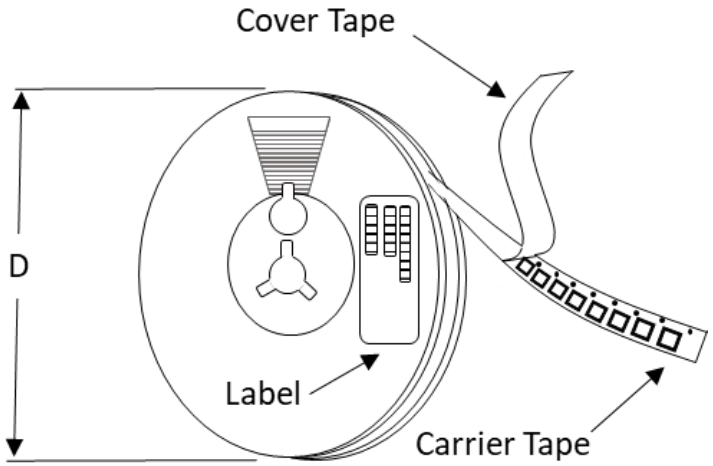
Dimensions (MM)	
A	1.5 +/- 0.050
B	1.5 +/- 0.050
C	.6 +/- 0.050
D	1.1 +/- 0.050
E	.5 Bsc
F	.2 +/- 0.050
G	.2 +/- 0.050
H	.45 +/- 0.050
J	.12 Ref.

1.5 mm DFN-6 Package Dimensions

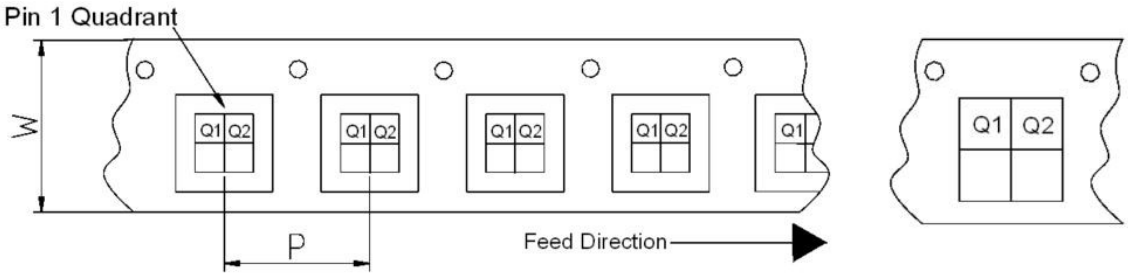
Tape and Reel Information:

Guerrilla RF's Tape and Reel specification complies with the Electronics Industries Association (EIA) standards for 'Embossed Carrier Tape of Surface Mount Components for Automatic Handling". Reference EIA-481. See the table on the following page for Tape and Reel specifications along with units per reel.

Devices are loaded with pins down into the carrier pocket with protective cover tape, wound into a plastic reel. Each reel will be packaged in a cardboard box. There will be product labels on the reel, the protective ESD bag and the outside surface of the box.



Tape and Reel Packaging with Reel Diameter Noted (D)



Carrier Tape Width (W), Pitch (P), Feed Direction and Pin 1 Quadrant Information

Tape and Reel Specification and Device Package Information Table

Package				Carrier Tape			Reel	
Type	Dimensions (mm)	Leads	Weight (mg)	Width (W) (mm)	Pocket Pitch (P) (mm)	Pin 1 Quad-rant	Diameter (D) (inches)	Units per Reel
QFN	2.0 x 2.0 x 0.50	12	7	8	4	Q1	7	2500
QFN	3.0 x 3.0 x 0.85	16	24	12	8	Q1	7	1500
DFN	1.5 x 1.5 x 0.45	6	4	8	4	Q1	7	2500
DFN	2.0 x 2.0 x 0.75	8	12	8	4	Q1	7	2500
LFM	3.5 x 3.5 x 0.75	See note	TBD	12	8	Q2	7	1500
LFM	4.0 x 4.0 x 0.75	See note	TBD	12	8	Q2	7	1500

Note: Lead count may vary. Reference applicable product data sheet

Data Sheet Release Status:	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry supplied transistor s-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on evaluation board measurements in the Guerrilla RF Applications Lab.
Released	All data based on device qualification data. Typically, this data is nearly identical to the data found in the preliminary version. Max and min values for key RF parameters are included.